

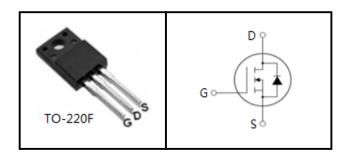
# **600V N-Channel MOSFET**

### FEATURES

- Fast switching
- Integrate fast recovery diode
- Fast switching speed
- 100% avalanche tested
- Improved dv/dt capability

### **APPLICATIONS**

- Switch Mode Power Supply (SMPS)
- Motor Controls
- Power Factor Correction (PFC)



Device Marking and Package Information			
Device	ce Package		
CSFR20N60F	TO-220F	CSFR20N60F	

<b>Absolute Maximum Ratings</b> $T_c = 25^{\circ}C$ , unless otherwise noted						
Devenester	Symbol	Value				
Parameter		TO-220F	Unit			
Drain-Source Voltage ( $V_{GS} = 0V$ )	V <sub>DSS</sub>	600	V			
Continuous Drain Current	I <sub>D</sub>	20	А			
Pulsed Drain Current (note1)	I <sub>DM</sub>	80	А			
Gate-Source Voltage	V <sub>GSS</sub>	±30	V			
Single Pulse Avalanche Energy (note2)	E <sub>AS</sub>	1201.3	mJ			
Avalanche Current (note1)	I <sub>AS</sub>	15.5	А			
Repetitive Avalanche Energy (note1)	E <sub>AR</sub>	720.8	mJ			
Power Dissipation ( $T_c = 25^{\circ}C$ )	P <sub>D</sub>	120	W			
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55~+150	٥C			

Thermal Resistance				
Peremeter	Symbol	Value	L lus i é	
Parameter	Symbol	TO-220F	Unit	
Thermal Resistance, Junction-to-Case	R <sub>thJC</sub>	1.04	00.00/	
Thermal Resistance, Junction-to-Ambient	R <sub>thJA</sub>	62.5	-  °C/W	



# CSFR20N60F

<b>Specifications</b> $T_J = 25^{\circ}C$ , unless otherwise noted								
Parameter	Ourseland	Test Osnelitions	Value			11		
	Symbol	Test Conditions	Min.	Тур.	Max.	Unit		
Static								
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0V, I_D = 250\mu A$	600			V		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 600V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1	μA		
Gate-Source Leakage	I <sub>GSS</sub>	$V_{GS}$ = $\pm 30V$			±100	nA		
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	3.0		4.0	V		
Drain-Source On-Resistance (Note3)	R <sub>DS(on)</sub>	$V_{GS} = 10V, I_{D} = 10A$		0.43	0.50	Ω		
Dynamic								
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V,		2718		pF		
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 25V,$		242				
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1.0MHz		24				
Total Gate Charge	Qg			75		nC		
Gate-Source Charge	Q <sub>gs</sub>	$V_{DD} = 480V, I_{D} = 20A, V_{GS} = 10V$		12				
Gate-Drain Charge	$Q_{gd}$			34				
Turn-on Delay Time	t <sub>d(on)</sub>			54		ns		
Turn-on Rise Time	t <sub>r</sub>	V <sub>DD</sub> = 250V, I <sub>D</sub> = 20A,		30				
Turn-off Delay Time	t <sub>d(off)</sub>	$R_{\rm G} = 25 \Omega$		313				
Turn-off Fall Time	t <sub>f</sub>			59				
Drain-Source Body Diode Character	istics							
Continuous Body Diode Current	۱ <sub>s</sub>				20	A		
Pulsed Diode Forward Current	I <sub>SM</sub>	T <sub>C</sub> = 25 °C			80			
Body Diode Voltage	V <sub>SD</sub>	$T_J = 25^{\circ}C, I_{SD} = 10A, V_{GS} = 0V$			1.4	V		
Reverse Recovery Time	t <sub>rr</sub>	V <sub>GS</sub> = 0V,I <sub>S</sub> = 20A,		154		ns		
Reverse Recovery Charge	Q <sub>rr</sub>	di <sub>F</sub> /dt =100A /µs		0.42		μC		

#### Notes

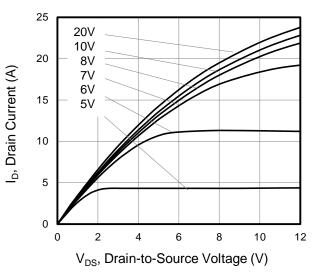
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L=10mH,  $V_{DD}$  = 50V,  $R_G$  = 25  $\Omega$ , Starting  $T_J$  = 25 °C
- 3. Pulse Test: Pulse width  $\leq$  300µs, Duty Cycle  $\leq$  1%

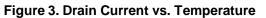


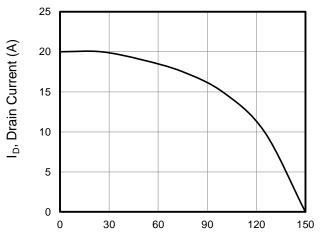
## **Typical Characteristics** $T_J = 25^{\circ}C$ , unless otherwise noted

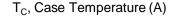
Figure 1. Output Characteristics ( $T_J = 25^{\circ}C$ )

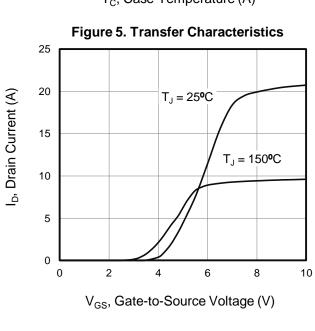
### Figure 2. Body Diode Forward Voltage

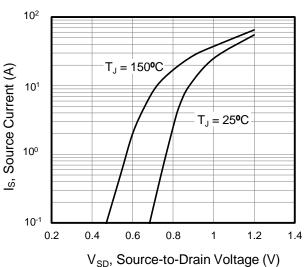














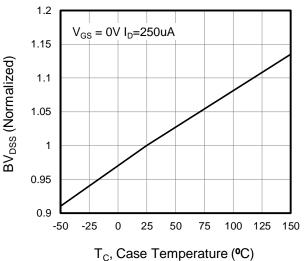
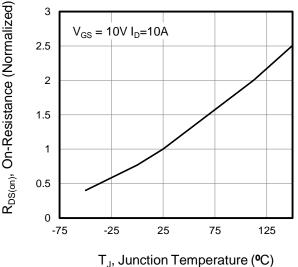


Figure 6. On-Resistance vs. Temperature





### **Typical Characteristics** $T_J = 25^{\circ}C$ , unless otherwise noted

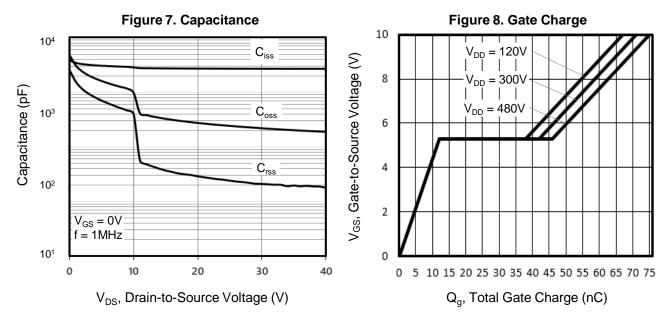
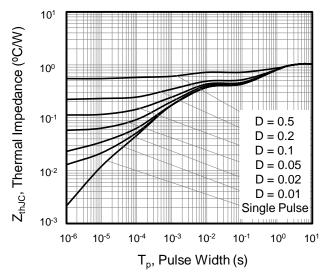


Figure 9. Transient Thermal Impedance

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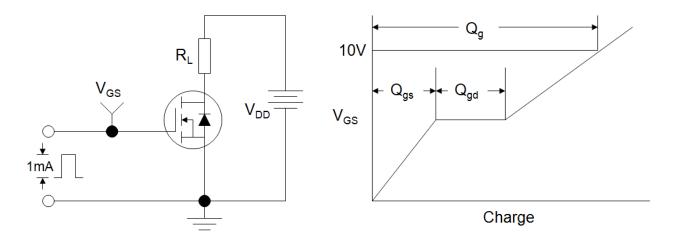


Figure B: Resistive Switching Test Circuit and Waveform

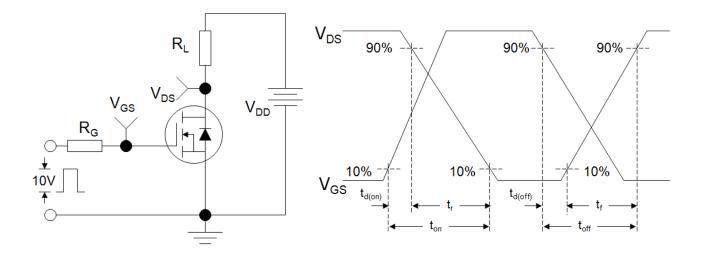
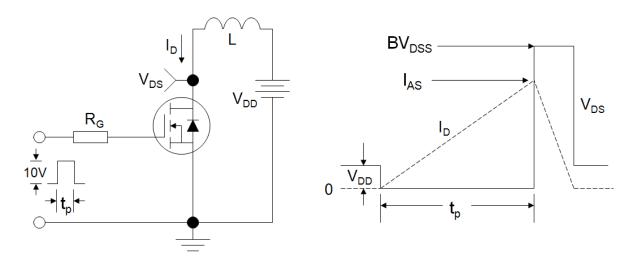


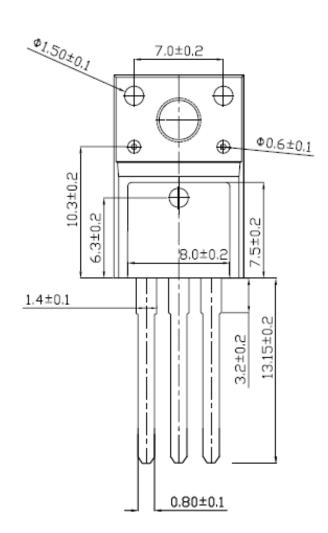
Figure C: Unclamped Inductive Switching Test Circuit and Waveform

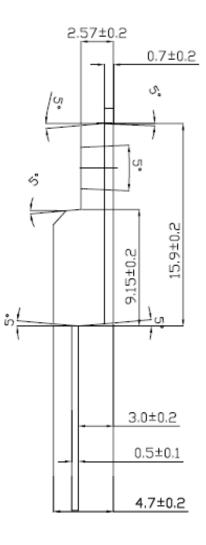






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